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Kind regards,

Team Nexperia



PIMN31 500 mA, 50 V NPN/NPN double resistor-equipped transistor; R1 = 1 k Ω , R2 = 10 k Ω

Rev. 01 — 19 June 2007

Product data sheet

1. Product profile

1.1 General description

500 mA, 50 V NPN/NPN double Resistor-Equipped Transistor (RET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

1.2 Features

- **500 mA output current capability**
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital application in automotive and industrial segments
- Switching loads

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
lo	output current		-	-	500	mA
R1	bias resistor 1 (input)		0.7	1	1.3	kΩ
R2/R1	bias resistor ratio		9	10	11	



1 | 2 3 *sym063*

500 mA, 50 V NPN/NPN double RET; R1 = 1 k Ω , R2 = 10 k Ω

2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1		
3	output (collector) TR2	0	
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1		

3. Ordering information

Table 3. Ord	lering inform	nation	
Type number	Package		
	Name	Description	Version
PIMN31	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457

4. Marking

Table 4. Marking codes	
Type number	Marking code
PIMN31	4E

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Per transistor V_{CBO} collector-base voltage open emitter - 50 V V_{CEO} collector-emitter voltage open base - 50 V V_{EBO} emitter-base voltage open collector - 50 V V_{EBO} input voltage open collector - 5 V v_1 input voltage - +12 V positive - -5 V l_0 output current - 500 mA						
VCBOcollector-base voltageopen emitter-50VVCEOcollector-emitter voltageopen base-50VVEBOemitter-base voltageopen collector-50VVIinput voltage-5Vpositive-+12Vnegative5VIooutput current-500mA	Symbol	Parameter	Conditions	Min	Max	Unit
V _{CEO} collector-emitter voltage open base - 50 V V _{EBO} emitter-base voltage open collector - 5 V V ₁ input voltage positive - +12 V negative - -5 V Io output current - 500 mA	Per transis	stor				
VEBO emitter-base voltage open collector - 5 V VI input voltage - +12 V positive - +12 V negative - -5 V Io output current - 500 mA	V _{CBO}	collector-base voltage	open emitter	-	50	V
VI input voltage - +12 V positive - +12 V negative - -5 V Io output current - 500 mA	V _{CEO}	collector-emitter voltage	open base	-	50	V
positive-+12Vnegative5VIooutput current-500mA	V _{EBO}	emitter-base voltage	open collector	-	5	V
$\begin{array}{c} -5 \\ \text{negative} \end{array} \qquad -5 \qquad \text{V} \\ I_{O} \qquad \text{output current} \qquad -500 \text{mA} \end{array}$	VI	input voltage				
I _O output current - 500 mA		positive		-	+12	V
		negative		-	-5	V
P_{tot} total power dissipation $T_{amb} \le 25 \ ^{\circ}C$ [1] - 290 mW	l _O	output current		-	500	mA
	P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	290	mW

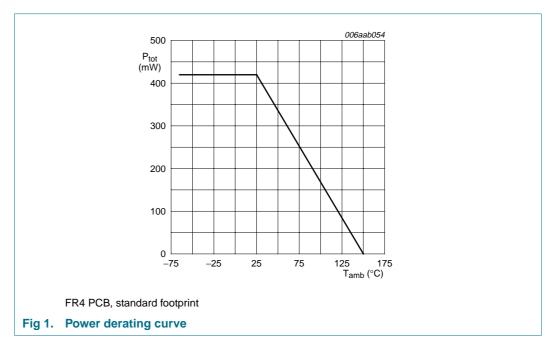
PIMN31

 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per device					
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	420	mW
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	431	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	105	K/W
Per devic	e					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	298	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

500 mA, 50 V NPN/NPN double RET; R1 = 1 k Ω , R2 = 10 k Ω

PIMN31

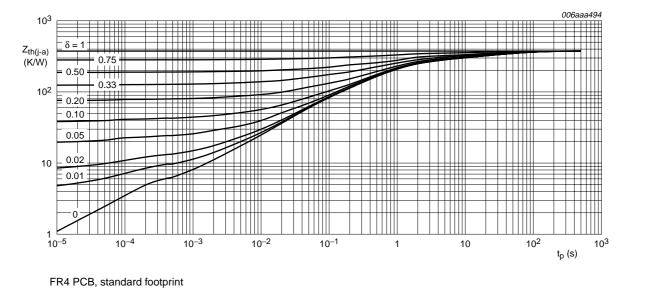


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT457 (SC-74); typical values

7. Characteristics

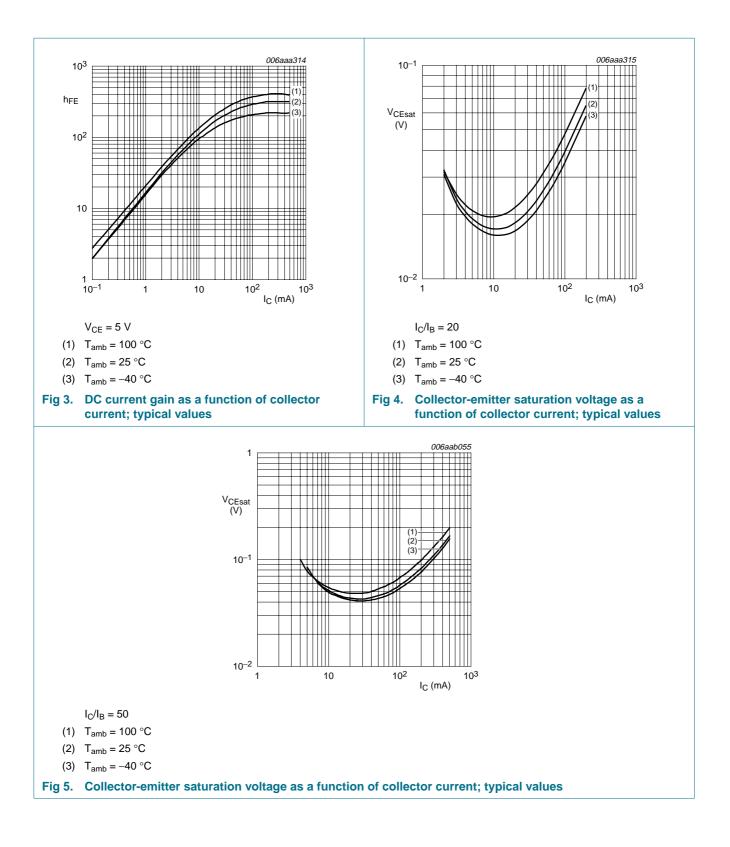
Table 7.Characteristics

 $T_{amb} = 25 \circ C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 50 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	-	-	0.5	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 V; I_C = 0 A$	-	-	0.72	mA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 50 \text{ mA}$	70	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = 50 mA; I_{B} = 2.5 mA	-	-	0.3	V
V _{I(off)}	off-state input voltage	V_{CE} = 5 V; I_{C} = 100 μA	0.3	0.6	1	V
V _{I(on)}	on-state input voltage	V_{CE} = 0.3 V; I _C = 20 mA	0.4	0.8	1.4	V
R1	bias resistor 1 (input)		0.7	1	1.3	kΩ
R2/R1	bias resistor ratio		9	10	11	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	7	-	pF

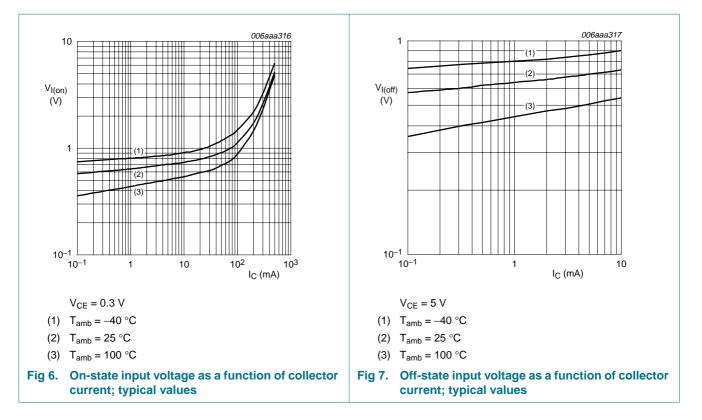
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500 mA, 50 V NPN/NPN double RET; R1 = 1 k Ω , R2 = 10 k Ω



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500 mA, 50 V NPN/NPN double RET; R1 = 1 k Ω , R2 = 10 k Ω



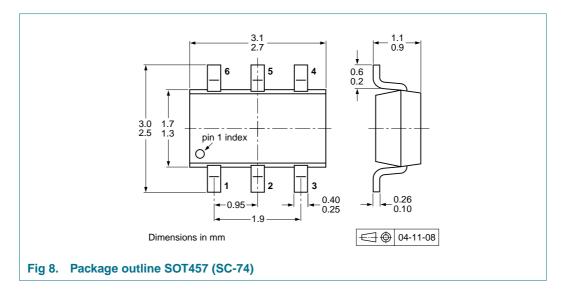
8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 (Stress qualification for discrete semiconductors) and is suitable for use in automotive critical applications.

500 mA, 50 V NPN/NPN double RET; R1 = 1 k Ω , R2 = 10 k Ω

9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing quantity	
				3000	10000
PIMN31	SOT457	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-165

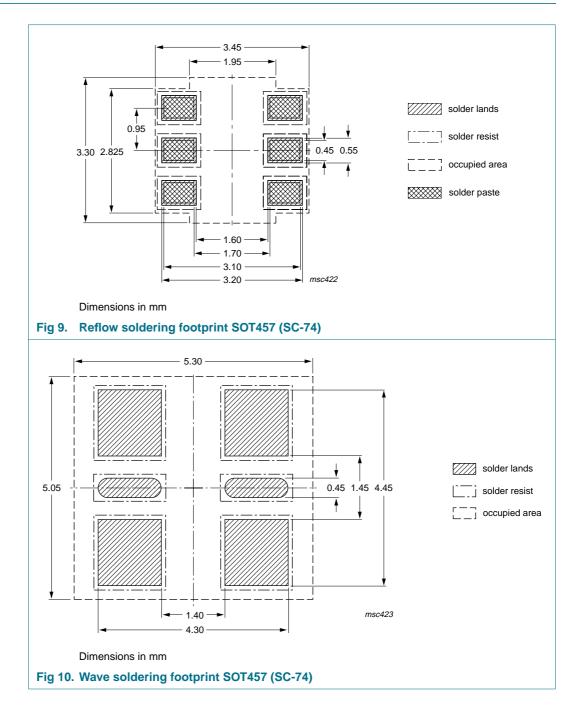
[1] For further information and the availability of packing methods, see <u>Section 14</u>.

[2] T1: normal taping

[3] T2: reverse taping

500 mA, 50 V NPN/NPN double RET; R1 = 1 k Ω , R2 = 10 k Ω

11. Soldering



500 mA, 50 V NPN/NPN double RET; R1 = 1 k Ω , R2 = 10 k Ω

12. Revision history

Table 9.	Revision histo	ory			
Document	ID	Release date	Data sheet status	Change notice	Supersedes
PIMN31_1		20070619	Product data sheet	-	-

PIMN31

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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PIMN31

500 mA, 50 V NPN/NPN double RET; R1 = 1 k Ω , R2 = 10 k Ω

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